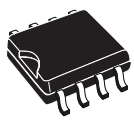
查询VN800供应商

VN800S(8961)
VN800PT(8961)

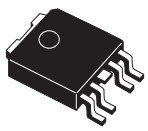
HIGH SIDE DRIVER

TYPE	$R_{DS(on)}$	I_{OUT}	V_{CC}
VN800S(8961) VN800PT(8961)	135 mΩ	1.2 A	36 V

- CMOS COMPATIBLE INPUT
- THERMAL SHUTDOWN
- CURRENT LIMITATION
- SHORTED LOAD PROTECTION
- UNDERVOLTAGE AND OVERVOLTAGE SHUTDOWN
- PROTECTION AGAINST LOSS OF GROUND
- VERY LOW STAND-BY CURRENT
- REVERSE BATTERY PROTECTION (*)



SO-8



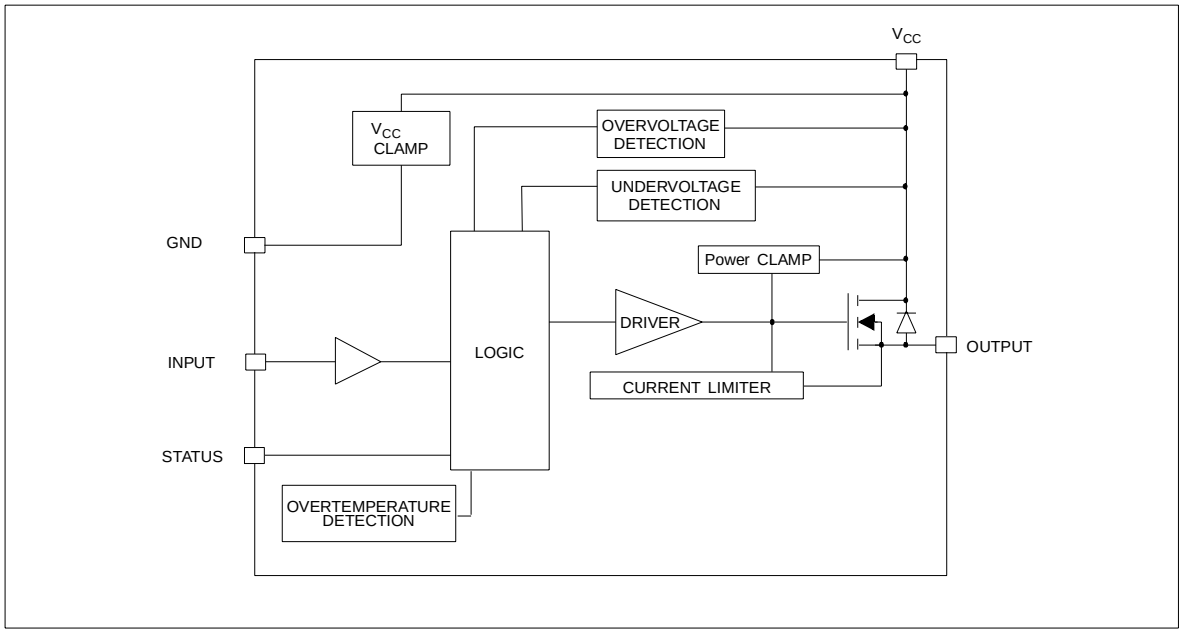
PPAK

ORDER CODES		
PACKAGE	**TUBE**	**T&R**
SO-8	VN800S(8961)	VN800S(8961)TR
PPAK	VN800PT(8961)	VN800PT(8961)TR

DESCRIPTION

The VN800S(8961), VN800PT(8961) are monolithic devices made by using STMicroelectronics VIPower M0-3 Technology, intended for driving any kind of load with one side connected to ground.
Active V_{CC} pin voltage clamp protects the device against low energy spikes (see ISO7637 transient compatibility table). Active current limitation combined with thermal shutdown and automatic restart protect the device against overload. Device automatically turns off in case of ground pin disconnection.

BLOCK DIAGRAM

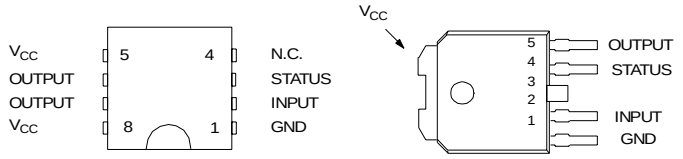


(*) See note at page 8

ABSOLUTE MAXIMUM RATING

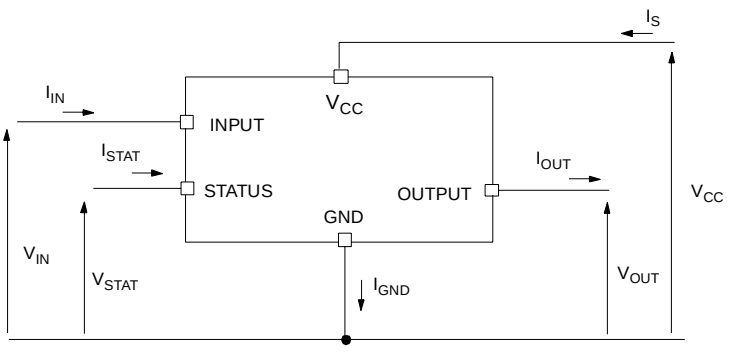
Symbol	Parameter	Value		Unit
		SO-8	PPAK	
V_{CC}	DC Supply Voltage	41		V
- V_{CC}	Reverse DC Supply Voltage	- 0.3		V
- I_{GND}	DC Reverse Ground Pin Current	- 200		mA
I_{OUT}	DC Output Current	Internally Limited		A
- I_{OUT}	Reverse DC Output Current	- 6		A
I_{IN}	DC Input Current	+/- 10		mA
V_{IN}	Input Voltage Range	-3/+V_{CC}		V
V_{STAT}	DC Status Voltage	+ V_{CC}		V
V_{ESD}	Electrostatic Discharge (Human Body Model: R=1.5KΩ; C=100pF) - INPUT - STATUS - OUTPUT - V_{CC}	 4000 4000 5000 5000		 V V V V
E_{MAX}	Maximum Switching Energy (L=77.5mH; R_L=0Ω; V_{bat}=13.5V; T_{jstart}=150ºC; I_L=1.5A)	121		mJ
E_{MAX}	Maximum Switching Energy (L=125mH; R_L=0Ω; V_{bat}=13.5V; T_{jstart}=150ºC; I_L=1.5A)		195	mJ
P_{tot}	Power Dissipation T_C=25°C	4.2	41.7	W
T_j	Junction Operating Temperature	Internally Limited		°C
T_c	Case Operating Temperature	- 40 to 150		°C
T_{stg}	Storage Temperature	- 55 to 150		°C
L_{max}	Max Inductive Load (V_{CC}=30V; R_{LOAD}=48Ω; T_{amb}=100°C; $Rth_{case>ambient}$≤25°C/W)		2	H

CONNECTION DIAGRAM (TOP VIEW)



SO-8 **PPAK**

CURRENT AND VOLTAGE CONVENTIONS



THERMAL DATA

Symbol	Parameter		Value		Unit
			SO-8	PPAK	
$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	-	3	°C/W
$R_{thj\text{-}lead}$	Thermal Resistance Junction-lead	Max	30	-	°C/W
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	93 (*)	78 (**)	°C/W

(*) When mounted on FR4 printed circuit board with 0.5 cm^2 of copper area (at least 35µ thick) connected to all V_{CC} pins.

(**) When mounted on FR4 printed circuit board with 0.5 cm^2 of copper area (at least 35µ thick).

ELECTRICAL CHARACTERISTICS ($8V<V_{CC}<36V$; $-40°C<T_j<150°C$, unless otherwise specified)

POWER

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{CC}	Operating Supply Voltage		5.5		36	V
V_{USD}	Undervoltage Shut-down		3	4	5.5	V
V_{OV}	Overvoltage Shut-down		36			V
R_{ON}	On State Resistance	I_{OUT} =0.5A; T_j=25°C			135	mΩ
		I_{OUT}=0.5A			270	mΩ
I_S	Supply Current	Off State; V_{CC}=24V; T_{case}=25°C		10	20	µA
		On State; V_{CC}=24V		1.5	3.5	mA
		On State; V_{CC}=24V; T_{case}=100°C			2.6	mA
I_{LGND}	Output Current at turn-off	$V_{CC}=V_{STAT}=V_{IN}=V_{GND}$=24V V_{OUT}=0V			1	mA
$I_{L(off1)}$	Off State Output Current	$V_{IN}=V_{OUT}$=0V	0		50	µA
$I_{L(off2)}$	Off State Output Current	$V_{IN}=V_{OUT}$=0V; Vcc=13V; T_j =125°C			5	µA
$I_{L(off3)}$	Off State Output Current	$V_{IN}=V_{OUT}$=0V; Vcc=13V; T_j =25°C			3	µA

SWITCHING (V_{CC}=24V)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	Turn-on Delay Time	R_L=48Ω from V_{IN} rising edge to V_{OUT}=2.4V		10		µs
$t_{d(off)}$	Turn-off Delay Time	R_L=48Ω from V_{IN} falling edge to V_{OUT}=21.6V		40		µs
$dV_{OUT}/dt_{(on)}$	Turn-on Voltage Slope	R_L=48Ω from V_{OUT}=2.4V to V_{OUT}=19.2V		See relative diagram		V/µs
$dV_{OUT}/dt_{(off)}$	Turn-off Voltage Slope	R_L=48Ω from V_{OUT}=21.6V to V_{OUT}=2.4V		See relative diagram		V/µs

INPUT PIN

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{INL}	Input Low Level				1.25	V
I_{INL}	Low Level Input Current	V_{IN}=1.25V	1			µA
V_{INH}	Input High Level		3.25			V
I_{INH}	High Level Input Current	V_{IN}=3.25V			10	µA
$V_{I(hyst)}$	Input Hysteresis Voltage		0.5			V
I_{IN}	Input Current	$V_{IN}=V_{CC}$=36V			200	µA

ELECTRICAL CHARACTERISTICS (continued)

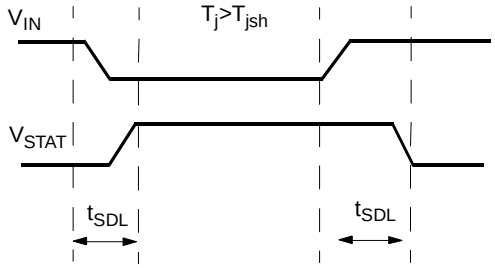
STATUS PIN

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{STAT}	Status Low Output Voltage	I_{STAT}=1.6 mA			0.5	V
I_{LSTAT}	Status Leakage Current	Normal Operation; V_{STAT}=V_{CC}=36 V			10	µA
C_{STAT}	Status Pin Input Capacitance	Normal Operation; V_{STAT}= 5V			30	pF

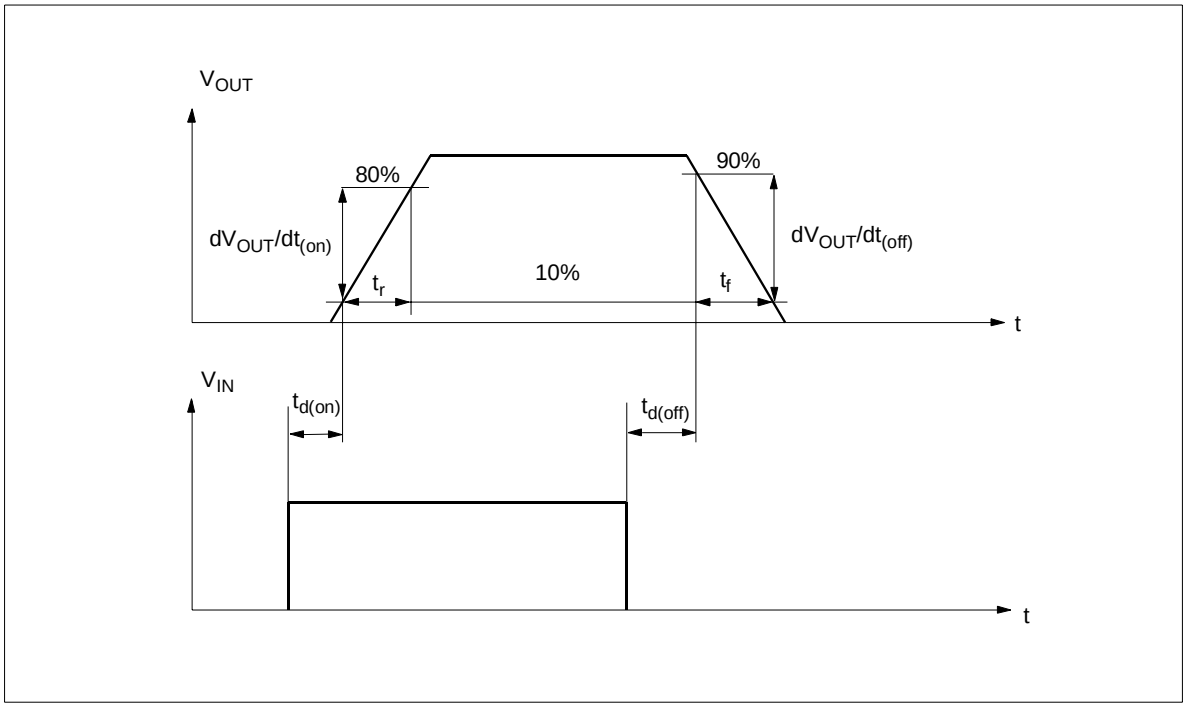
PROTECTIONS

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
T_{TSD}	Shut-down Temperature		150	175	200	°C
T_R	Reset Temperature		135			°C
T_{hyst}	Thermal Hysteresis		7	15		°C
T_{SDL}	Status Delay in Overload Condition	T_j>T_{jsh}			20	µs
I_{lim}	DC Short Circuit Current	V_{CC}=16V; R_{LOAD}=10mΩ	1.2		2	A
V_{demag}	Turn-off Output Clamp Voltage	I_{OUT}=0.5 A; L=6mH	V_{CC}-47	V_{CC}-52	V_{CC}-57	V

OVERTEMP STATUS TIMING



Switching time Waveforms



TRUTH TABLE

CONDITIONS	INPUT	OUTPUT	STATUS
Normal Operation	L H	L H	H H
Current Limitation	L H H	L X X	H ($T_j < T_{TSD}$) H ($T_j > T_{TSD}$) L
Overtemperature	L H	L L	H L
Undervoltage	L H	L L	X X
Overvoltage	L H	L L	H H

Figure 1: Peak Short Circuit Current Test Circuit

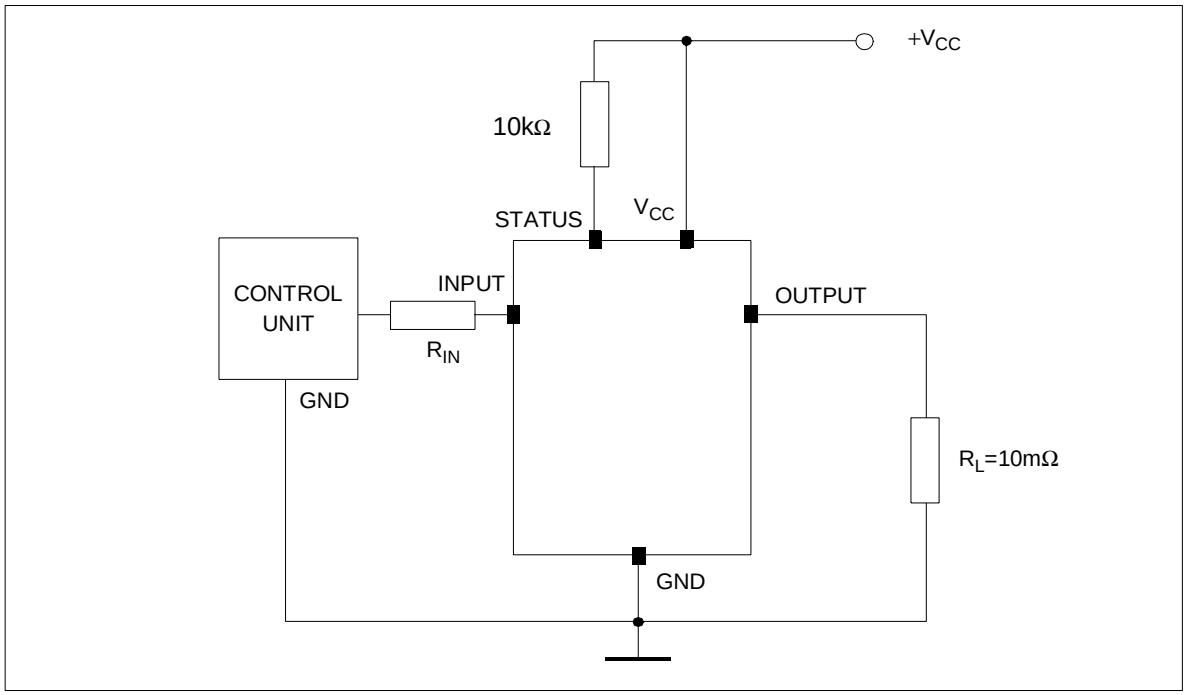
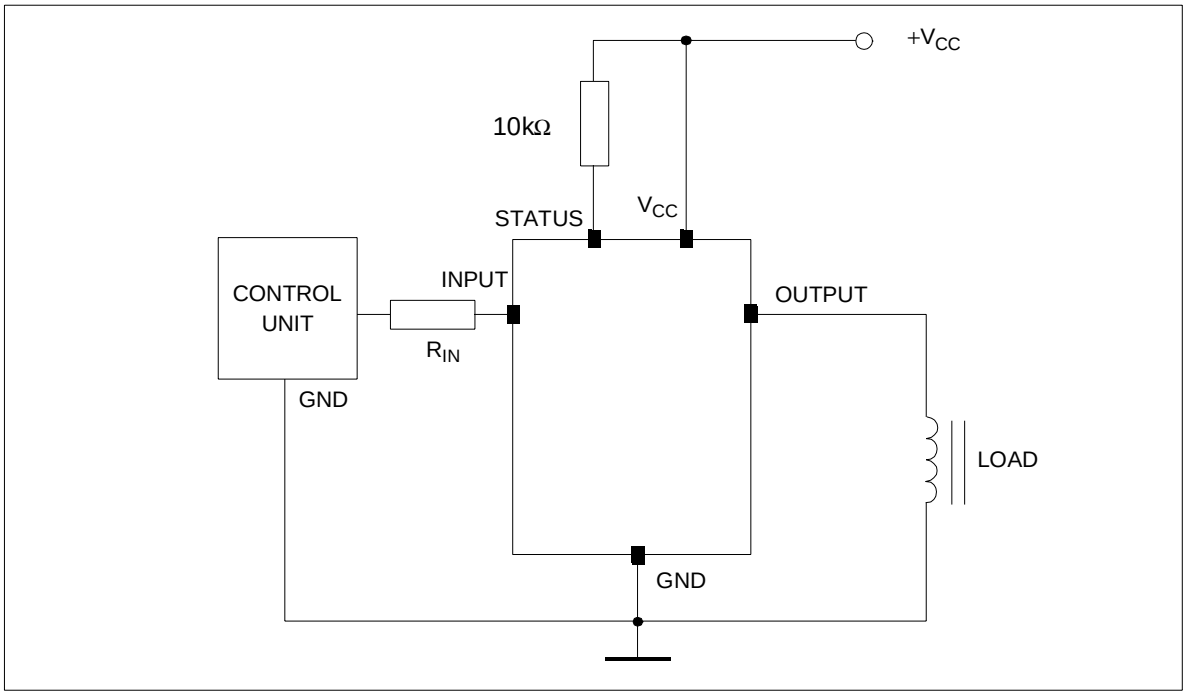


Figure 2: Avalanche Energy Test Circuit



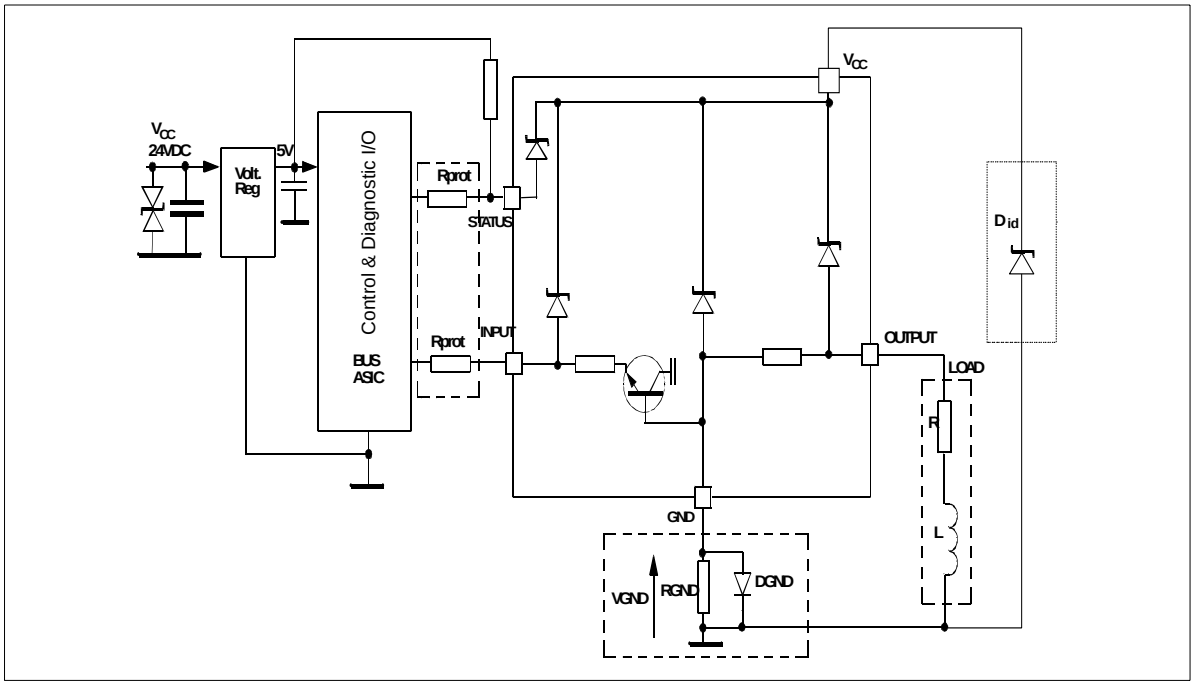
ELECTRICAL TRANSIENT REQUIREMENTS ON V_{CC} PIN

ISO T/R 7637/1 Test Pulse	TEST LEVELS				
	I	II	III	IV	Delays and Impedance
1	-25 V	-50 V	-75 V	-100 V	2 ms 10 Ω
2	+25 V	+50 V	+75 V	+100 V	0.2 ms 10 Ω
3a	-25 V	-50 V	-100 V	-150 V	0.1 µs 50 Ω
3b	+25 V	+50 V	+75 V	+100 V	0.1 µs 50 Ω
4	-4 V	-5 V	-6 V	-7 V	100 ms, 0.01 Ω
5	+26.5 V	+46.5 V	+66.5 V	+86.5 V	400 ms, 2 Ω

ISO T/R 7637/1 Test Pulse	TEST LEVELS RESULTS			
	I	II	III	IV
1	C	C	C	C
2	C	C	C	C
3a	C	C	C	C
3b	C	C	C	C
4	C	C	C	C
5	C	E	E	E

CLASS	CONTENTS
C	All functions of the device are performed as designed after exposure to disturbance.
E	One or more functions of the device is not performed as designed after exposure to disturbance and cannot be returned to proper operation without replacing the device.

APPLICATION SCHEMATIC



GND PROTECTION NETWORK AGAINST REVERSE BATTERY

Solution 1: Resistor in the ground line (R_{GND} only). This can be used with any type of load.

The following is an indication on how to dimension the R_{GND} resistor.

1) $R_{GND} \leq 600mV / (I_{S(on)max})$.

2) $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

where $-I_{GND}$ is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device's datasheet.

Power Dissipation in R_{GND} (when V_{CC}<0: during reverse battery situations) is:

$P_D= (-V_{CC})^2/R_{GND}$

This resistor can be shared amongst several different HSD. Please note that the value of this resistor should be calculated with formula (1) where $I_{S(on)max}$ becomes the sum of the maximum on-state currents of the different devices.

Please note that if the microprocessor ground is not common with the device ground then the R_{GND} will produce a shift ($I_{S(on)max}$ * R_{GND}) in the input thresholds and the status output values. This shift will vary depending on many devices are ON in the case of several high side drivers sharing the same R_{GND}.

If the calculated power dissipation leads to a large resistor or several devices have to share the same resistor then the ST suggests to utilize Solution 2 (see below).

Solution 2: A diode (D_{GND}) in the ground line.

A resistor (R_{GND}=1kΩ) should be inserted in parallel to D_{GND} if the device will be driving an inductive load.

This small signal diode can be safely shared amongst several different HSD. Also in this case, the presence of the ground network will produce a shift (≃600mV) in the input threshold and the status output values if the microprocessor ground is not common with the device ground. This shift will not vary if more than one HSD shares the same diode/resistor network.

LOAD DUMP PROTECTION

D_{ld} is necessary (Voltage Transient Suppressor) if the load dump peak voltage exceeds V_{CC} max DC rating. The same applies if the device will be subject to transients on the V_{CC} line that are greater than the ones shown in the ISO T/R 7637/1 table.

µC I/Os PROTECTION:

If a ground protection network is used and negative transients are present on the V_{CC} line, the control pins will be pulled negative. ST suggests to insert a resistor (R_{prot}) in line to prevent the µC I/Os pins to latch-up.

The value of these resistors is a compromise between the leakage current of µC and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit of µC I/Os.

$-V_{CCpeak}/I_{latchup} \leq R_{prot} \leq (V_{OH\mu C}-V_{IH}-V_{GND}) / I_{IHmax}$

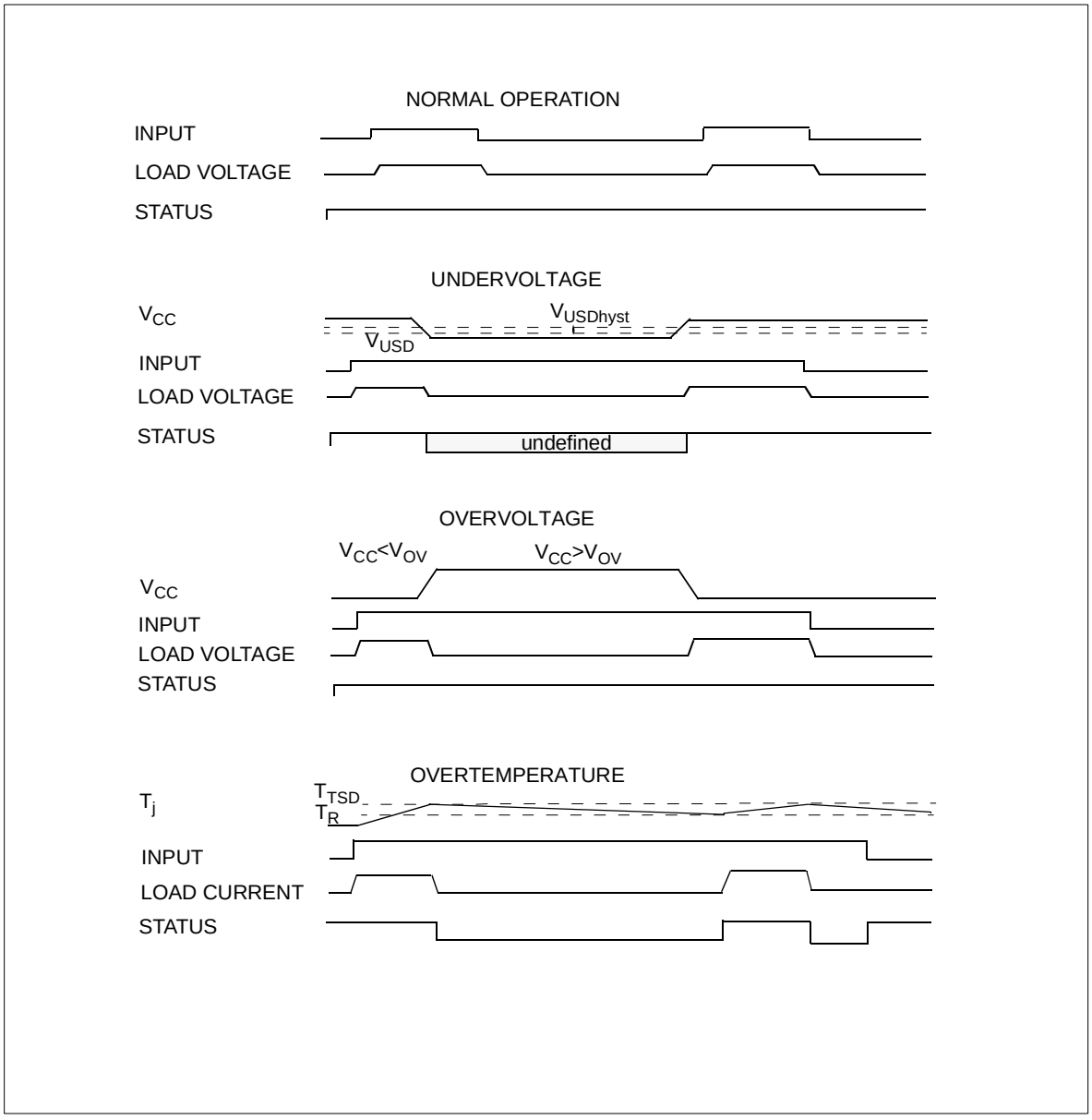
Calculation example:

For V_{CCpeak}= - 100V and $I_{latchup} \geq$ 20mA; $V_{OH\mu C} \geq$ 4.5V

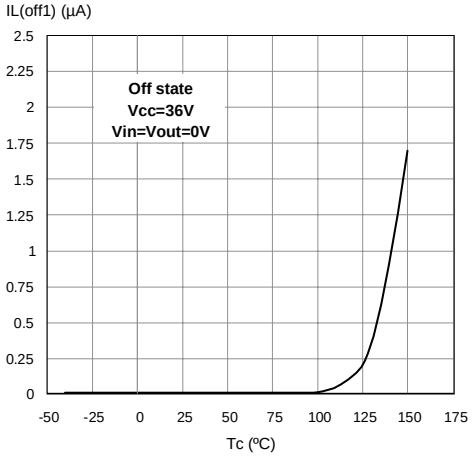
5kΩ ≤ R_{prot} ≤ 65kΩ.

Recommended R_{prot} value is 10kΩ.

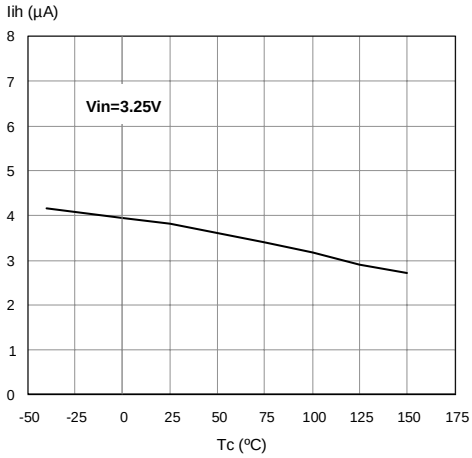
Figure 3: Waveforms



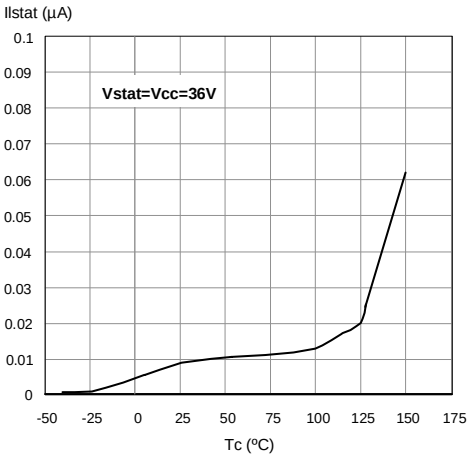
Off State Output Current



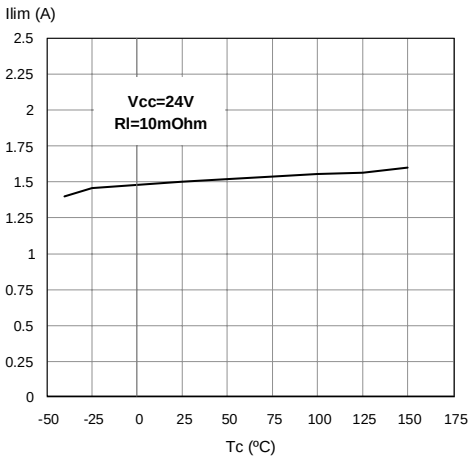
High Level Input Current



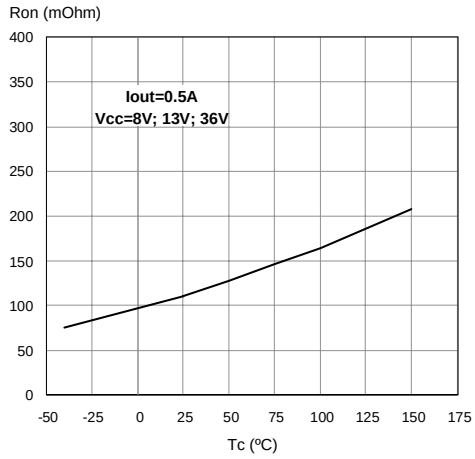
Status Leakage Current



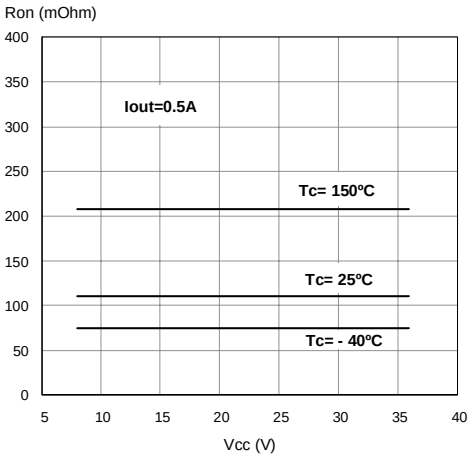
I_{LIM} Vs T_{case}



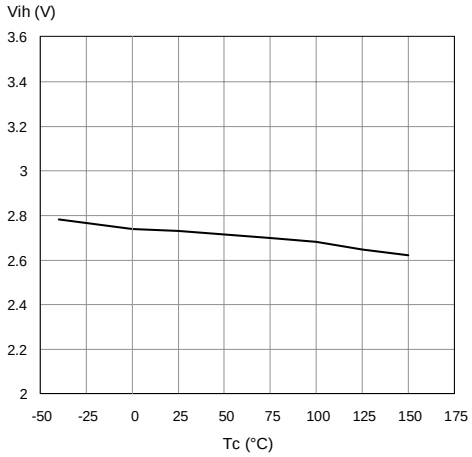
On State Resistance Vs T_{case}



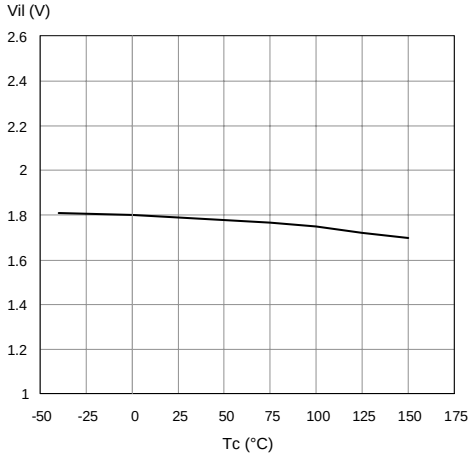
On State Resistance Vs V_{CC}



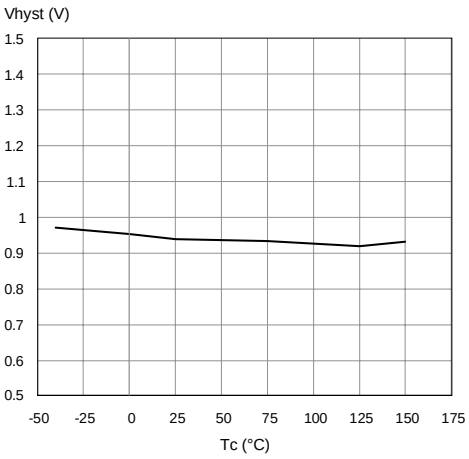
Input High Level



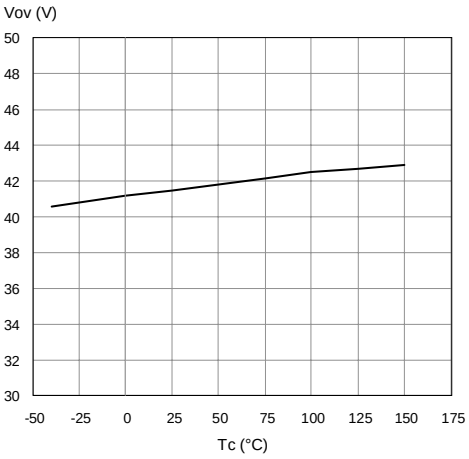
Input Low Level



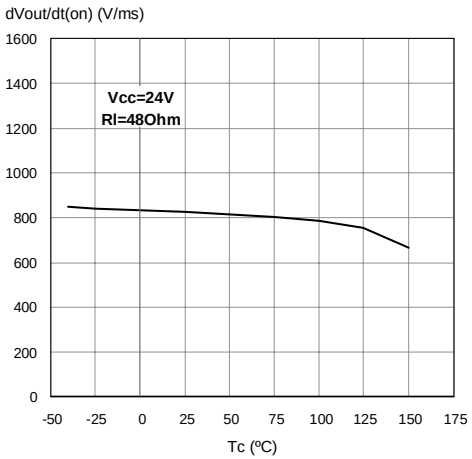
Input Hysteresis Voltage



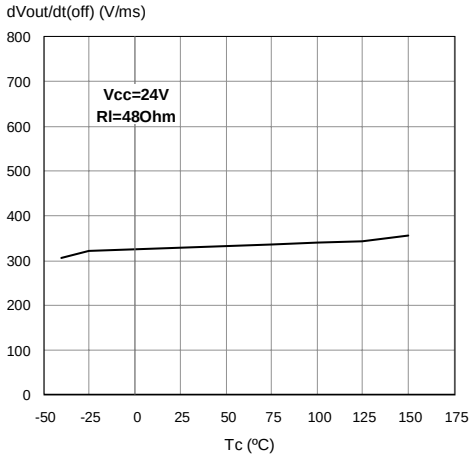
Overvoltage Shutdown



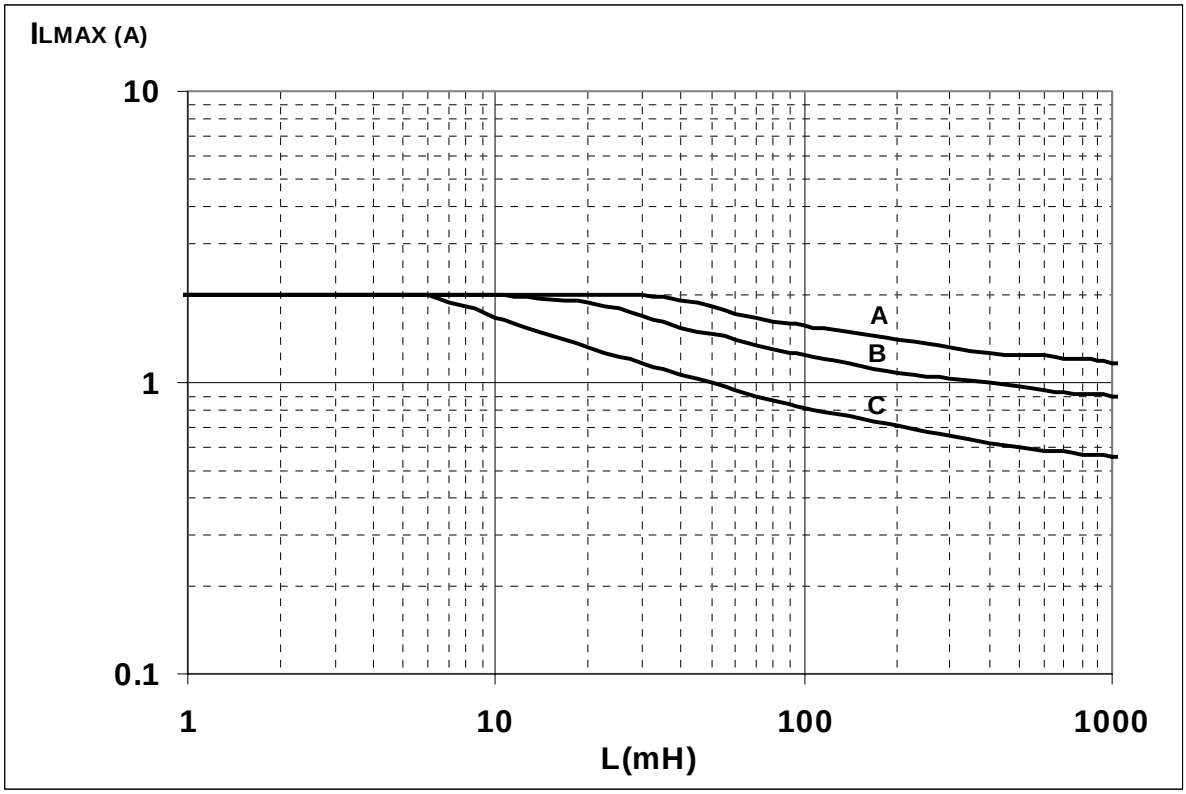
Turn-on Voltage Slope



Turn-off Voltage Slope



PPAK Maximum turn off current versus load inductance



A = Single Pulse at T_{Jstart}=150ºC

B= Repetitive pulse at T_{Jstart}=100ºC

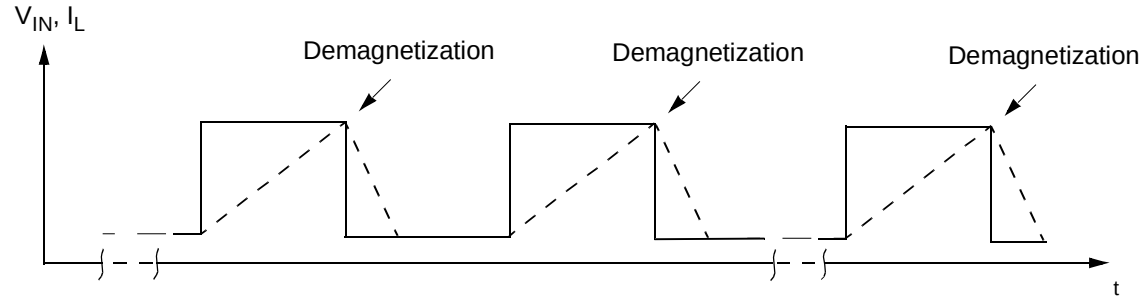
C= Repetitive Pulse at T_{Jstart}=125ºC

Conditions:

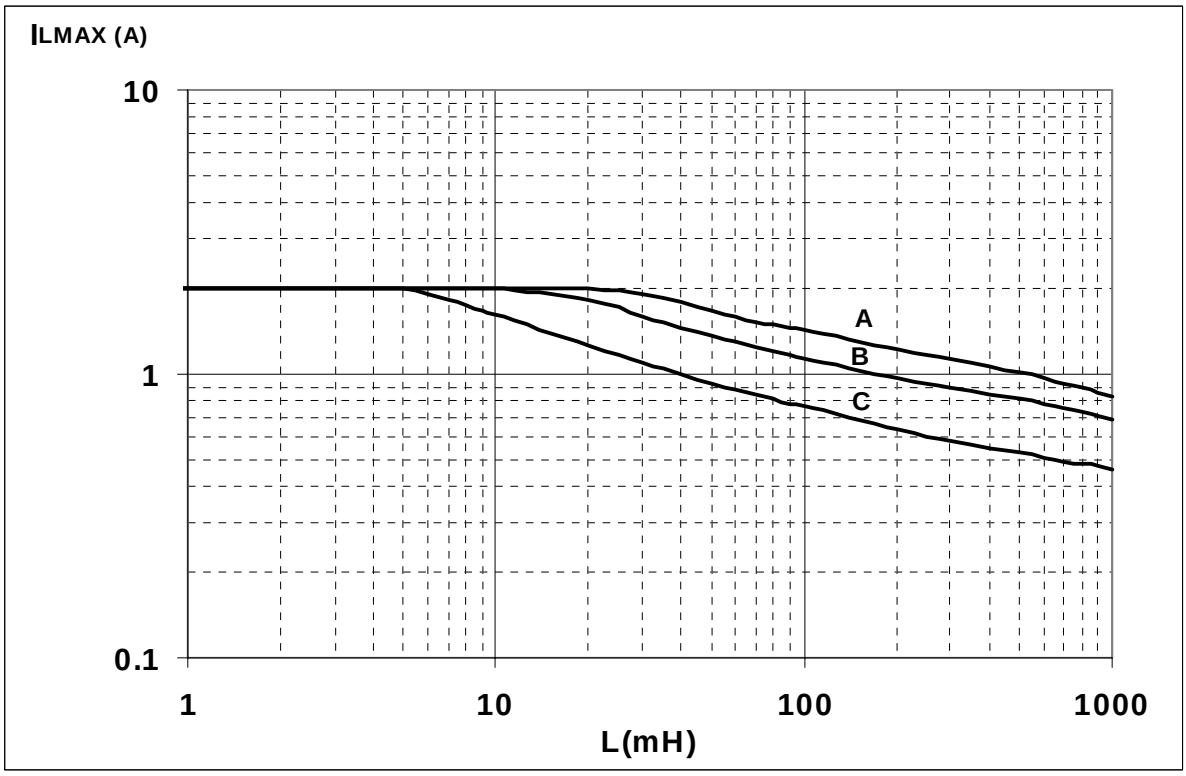
V_{CC}=13.5V

Values are generated with R_L=0Ω

In case of repetitive pulses, T_{jstart} (at beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves B and C.



SO-8 Maximum turn off current versus load inductance



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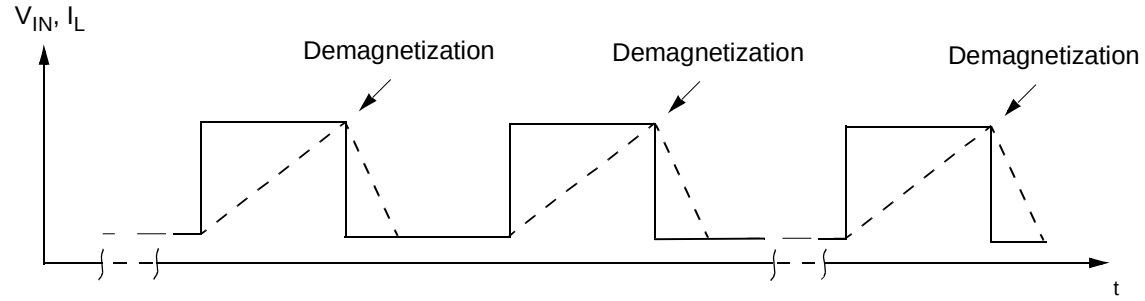
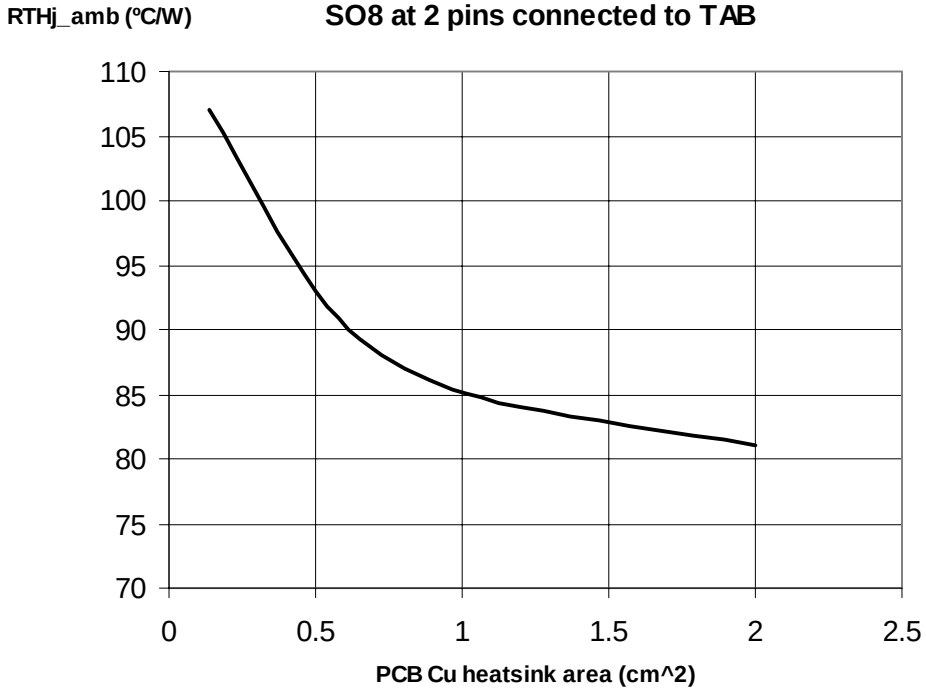


SO-8 THERMAL DATA

SO-8 PC Board

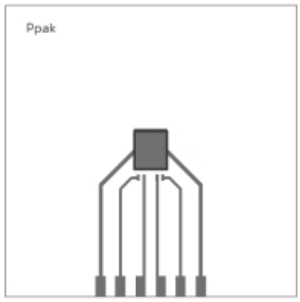
Layout condition of R_{th} and Z_{th} measurements (PCB FR4 area= 58mm x 58mm, PCB thickness=2mm, Cu thickness=35µm, Copper areas: 0.14cm^2, 2cm^2).

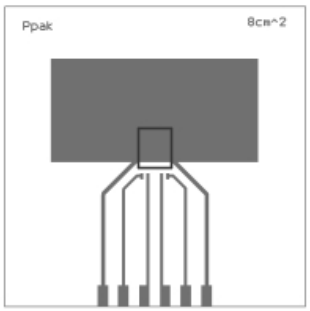
$R_{thj\text{-}amb}$ Vs PCB copper area in open box free air condition



PPAK THERMAL DATA

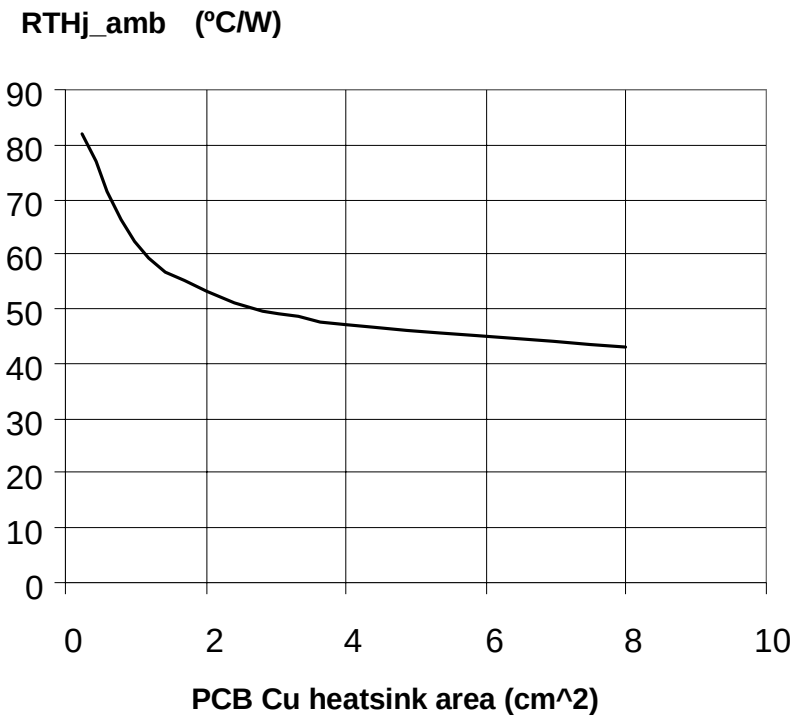
PPAK PC Board



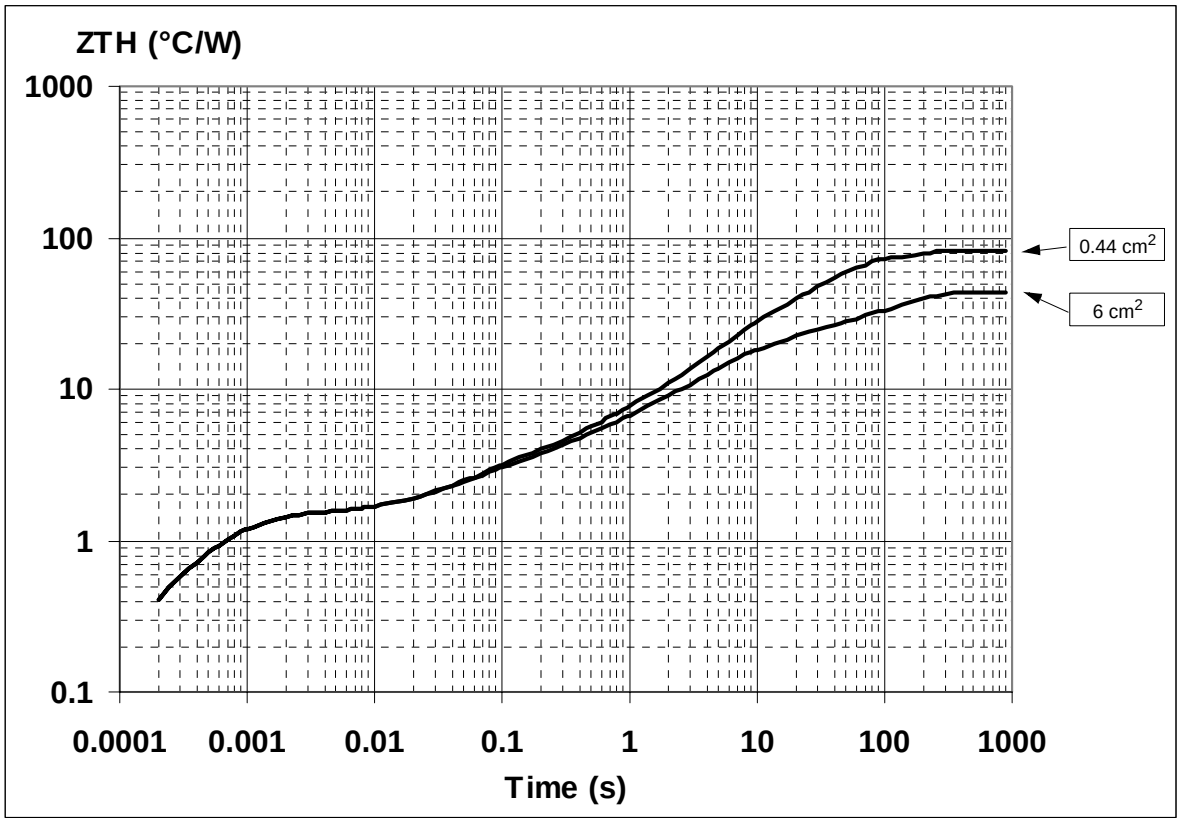


Layout condition of R_{th} and Z_{th} measurements (PCB FR4 area= 60mm x 60mm, PCB thickness=2mm, Cu thickness=35µm, Copper areas: 0.44cm^2, 8cm^2).

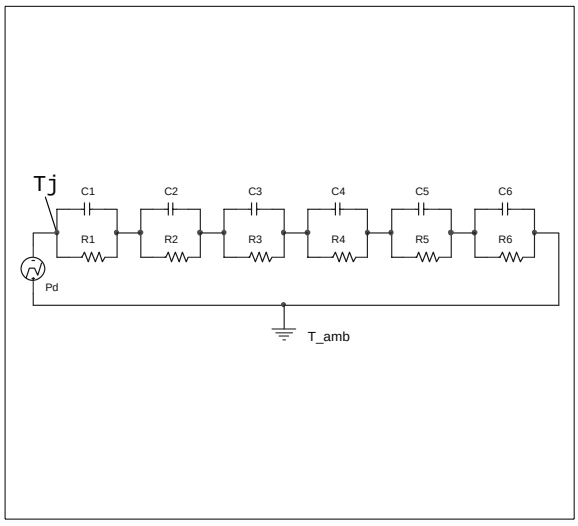
$R_{thj\text{-}amb}$ Vs PCB copper area in open box free air condition



PPAK Thermal Impedance Junction Ambient Single Pulse



Thermal fitting model of a single channel HSD in PPAK



Pulse calculation formula

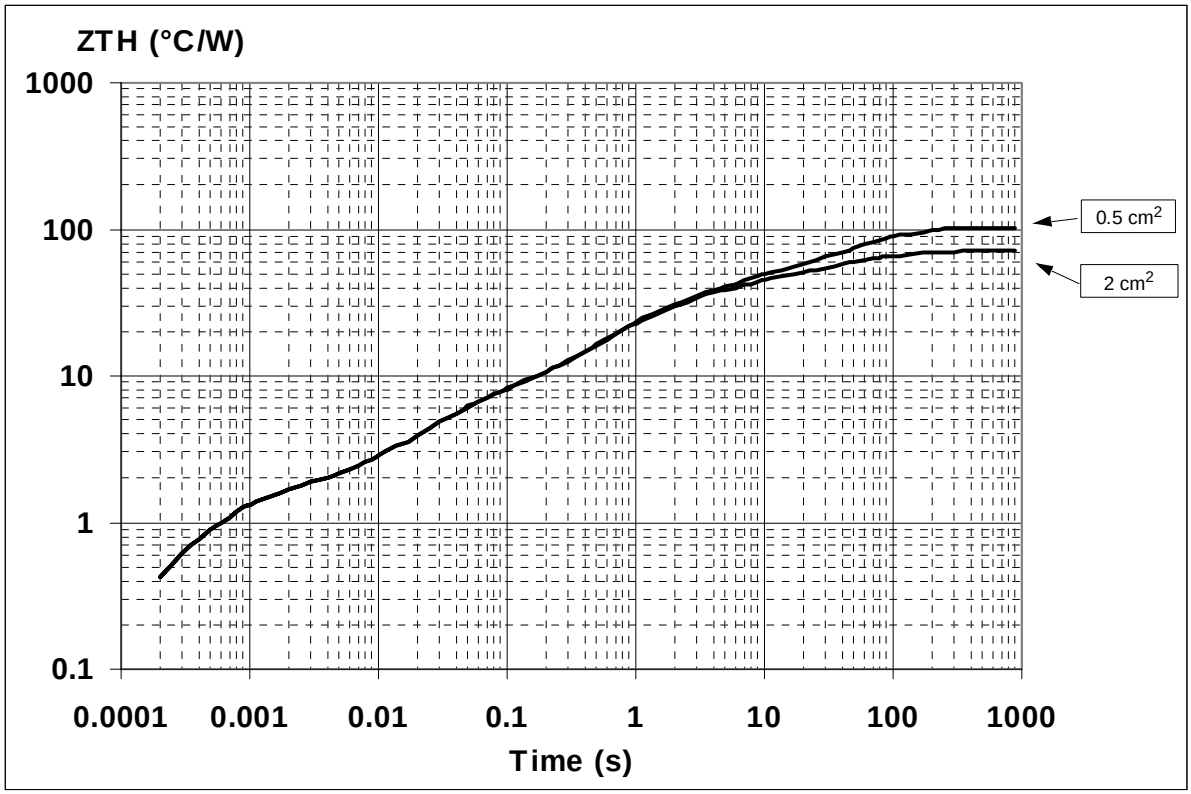
$$Z_{TH\delta} = R_{TH} \cdot \delta + Z_{THtp}(1 - \delta)$$

where $\delta = t_p / T$

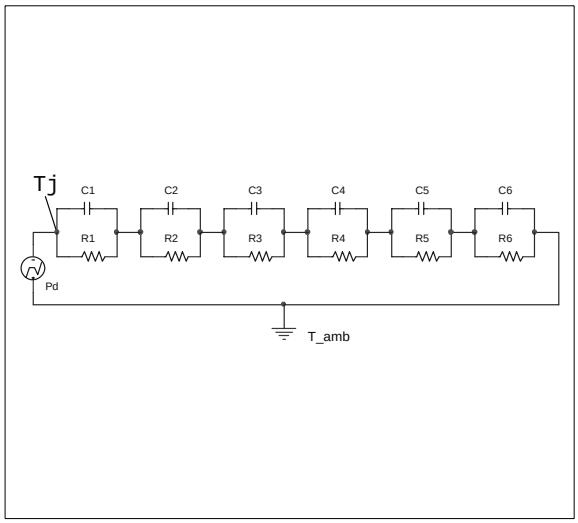
Thermal Parameter

Area/island (cm²)	0.44	6
R1 (°C/W)	0.04	
R2 (°C/W)	0.25	
R3 (°C/W)	0.3	
R4 (°C/W)	2	
R5 (°C/W)	15	
R6 (°C/W)	61	24
C1 (W.s/°C)	0.0008	
C2 (W.s/°C)	0.007	
C3 (W.s/°C)	0.02	
C4 (W.s/°C)	0.3	
C5 (W.s/°C)	0.45	
C6 (W.s/°C)	0.8	5

SO-8 Thermal Impedance Junction Ambient Single Pulse



Thermal fitting model of a single channel HSD in SO-8



Pulse calculation formula

$$Z_{TH\delta} = R_{TH} \cdot \delta + Z_{THtp}(1-\delta)$$

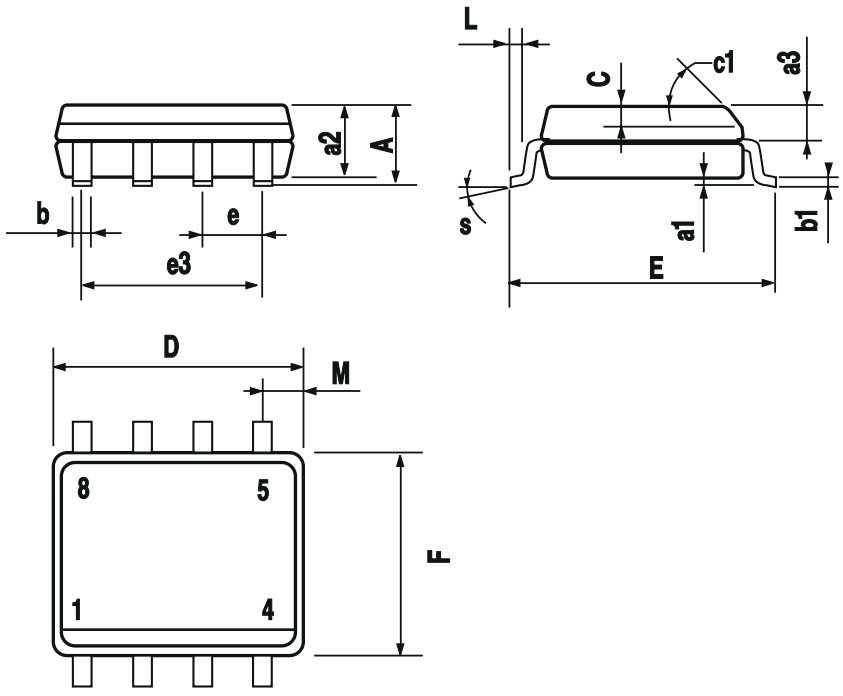
where $\delta = t_p / T$

Thermal Parameter

Area/island (cm^2)	0.14	2
R1 (°C/W)	0.24	
R2 (°C/W)	1.2	
R3 (°C/W)	4.5	
R4 (°C/W)	21	
R5 (°C/W)	16	
R6 (°C/W)	58	28
C1 (W.s/°C)	0.00015	
C2 (W.s/°C)	0.0005	
C3 (W.s/°C)	7.50E-03	
C4 (W.s/°C)	0.045	
C5 (W.s/°C)	0.35	
C6 (W.s/°C)	1.05	2

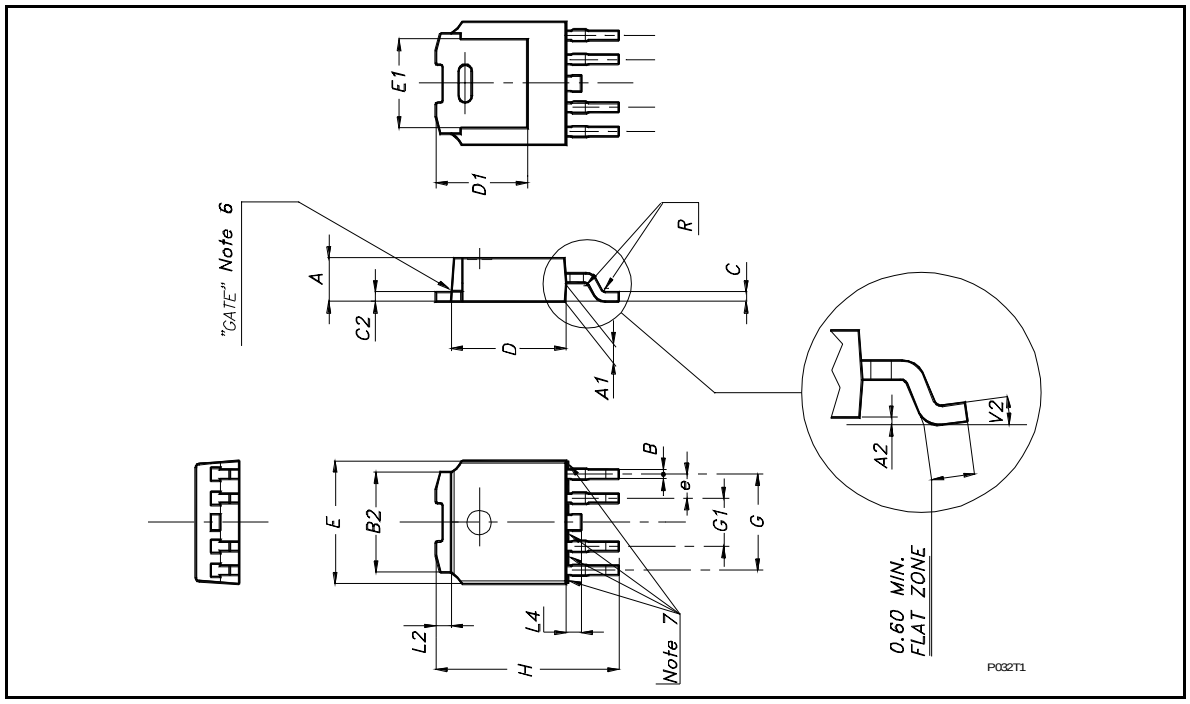
SO-8 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					
L1	0.8		1.2	0.031		0.047

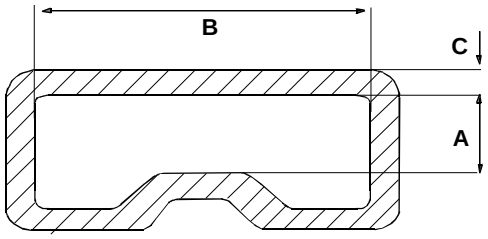


PPAK MECHANICAL DATA

DIM.	MIN.	TYP	MAX.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
B	0.40		0.60
B2	5.20		5.40
C	0.45		0.60
C2	0.48		0.60
D1		5.1	
D	6.00		6.20
E	6.40		6.60
E1		4.7	
e		1.27	
G	4.90		5.25
G1	2.38		2.70
H	9.35		10.10
L2		0.8	1.00
L4	0.60		1.00
R		0.2	
V2	0°		8°
Package Weight	Gr. 0.3		



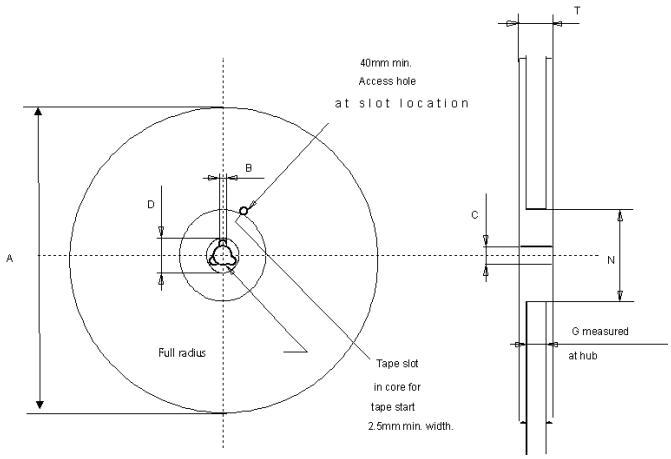
SO-8 TUBE SHIPMENT (no suffix)



Base Q.ty	100
Bulk Q.ty	2000
Tube length (± 0.5)	532
A	3.2
B	6
C (± 0.1)	0.6

All dimensions are in mm.

TAPE AND REEL SHIPMENT (suffix "13TR")



REEL DIMENSIONS

Base Q.ty	2500
Bulk Q.ty	2500
A (max)	330
B (min)	1.5
C (± 0.2)	13
F	20.2
G (+ 2 / -0)	12.4
N (min)	60
T (max)	18.4

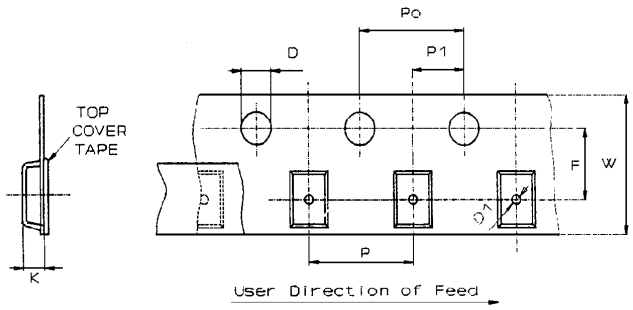
All dimensions are in mm.

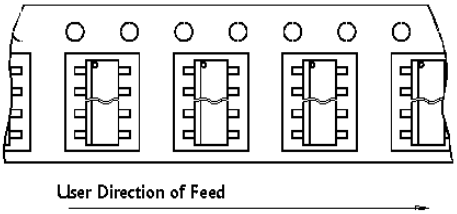
TAPE DIMENSIONS

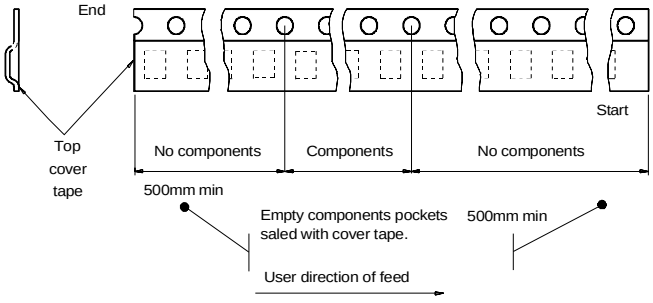
According to Electronic Industries Association (EIA) Standard 481 rev. A, Feb 1986

Tape width	**W**	12
Tape Hole Spacing	**P0 (± 0.1)**	4
Component Spacing	**P**	8
Hole Diameter	**D (± 0.1/-0)**	1.5
Hole Diameter	**D1 (min)**	1.5
Hole Position	**F (± 0.05)**	5.5
Compartment Depth	**K (max)**	4.5
Hole Spacing	**P1 (± 0.1)**	2

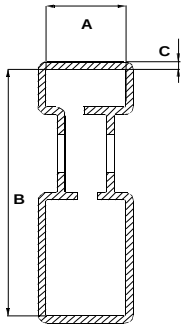
All dimensions are in mm.







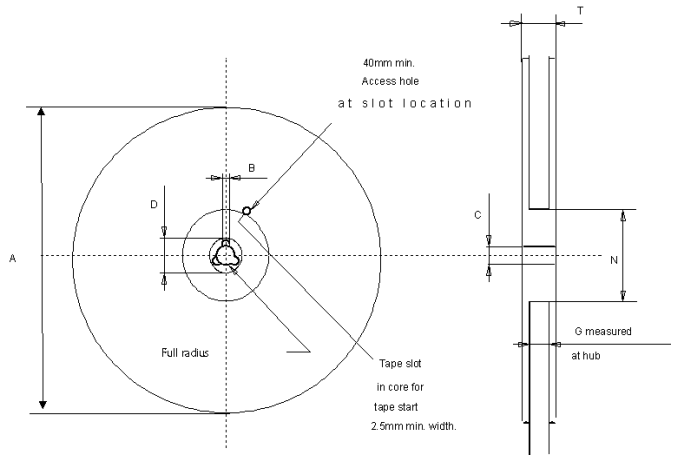
PPAK TUBE SHIPMENT (no suffix)



Base Q.ty	75
Bulk Q.ty	3000
Tube length (± 0.5)	532
A	6
B	21.3
C (± 0.1)	0.6

All dimensions are in mm.

TAPE AND REEL SHIPMENT (suffix "13TR")



REEL DIMENSIONS

Base Q.ty	2500
Bulk Q.ty	2500
A (max)	330
B (min)	1.5
C (± 0.2)	13
F	20.2
G (+ 2 / -0)	16.4
N (min)	60
T (max)	22.4

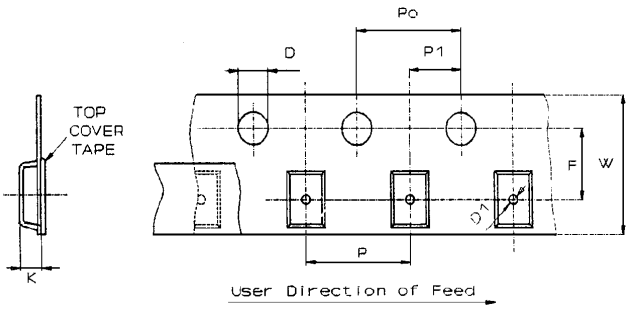
All dimensions are in mm.

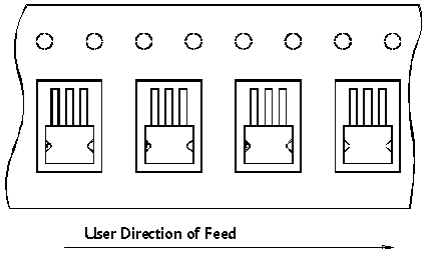
TAPE DIMENSIONS

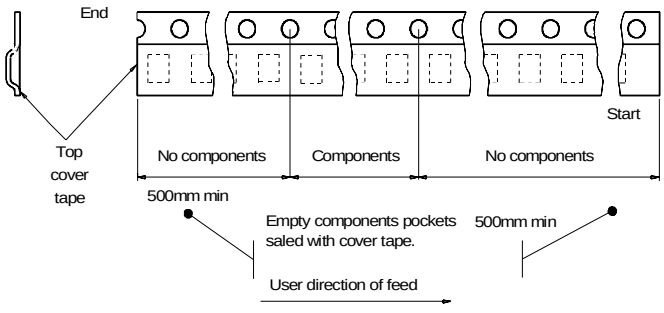
According to Electronic Industries Association (EIA) Standard 481 rev. A, Feb 1986

Tape width	**W**	16
Tape Hole Spacing	**P0 (± 0.1)**	4
Component Spacing	**P**	8
Hole Diameter	**D (± 0.1/-0)**	1.5
Hole Diameter	**D1 (min)**	1.5
Hole Position	**F (± 0.05)**	7.5
Compartment Depth	**K (max)**	6.5
Hole Spacing	**P1 (± 0.1)**	2

All dimensions are in mm.







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